

1 BURNER FOR FABRICATING AEROSOL DOPED WAVEGUIDES

2
3 FIELD OF THE INVENTION

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5 This invention relates to a burner for fabricating
6 aerosol doped waveguides. In particular, the invention
7 relates to a modified burner which enables the in-situ
8 delivery of dopant ions in a single step process to an
9 optical waveguide during the deposition stage of
10 fabrication.

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12 BACKGROUND OF THE INVENTION

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14 The fabrication of silica based planar waveguides with
15 high ion content by chemical vapour deposition (CVD),
16 and in particular flame hydrolysis deposition (FHD)
17 methods, is already known in the art.

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19 In such fabrication methods it is often desired to
20 introduce dopant ions during the deposition process.
21 The introduction of dopant ions is effected by a number
22 of known methods which suffer to a greater or lesser
23 degree from certain disadvantages. For example,
24 solution doping requires the core which makes up the
25 waveguide to be partially fused and this introduces

1 several complications.

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3 An alternative method is to use aerosol doping. In
4 aerosol doping droplets of an aqueous solution of the
5 dopant ions are transferred to a modified FHD burner.
6 The water is evaporated to leave submicron dopant ion
7 particles. The dopant ions are then oxidised in the
8 burner flame and can be distributed during the
9 deposition stage of fabricating the waveguide.

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11 It is known to modify conventional FHD burners to
12 incorporate an extra port for the aerosol feed. A
13 problem arises, however, when such burners are used in
14 the fabrication of heavily doped waveguides. High
15 dopant ion levels require high concentrations of the
16 aqueous dopant ion solution. During the evaporation of
17 the solvent in highly concentrated solutions, more
18 dopant ions condense around the aerosol inlet port than
19 would do with a less concentrated solution. This build
20 up of condensed ions can create blockages. The present
21 invention seeks to provide a modified burner design
22 which obviates or mitigates the problems heretofore
23 mentioned.

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25 SUMMARY OF THE INVENTION

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27 In accordance with the present invention there is
28 provided a burner for fabricating aerosol doped
29 waveguides, the burner including:

30 a plurality of inlet ports each connected to a
31 respective torch conduit, said torch conduit connecting
32 its respective inlet port to a gas mixing region; and
33 including a gas expansion chamber provided for at least
34 one of said inlet ports upstream of said gas mixing
35 region.

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1 other inlet ports.

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3 Preferably, said at least one inlet port is orientated
4 at a first angle with respect to the burner axis, and
5 wherein the other inlet ports are orientated at a
6 second angle with respect to the burner axis, said
7 first angle being less than said second angle.

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9 Preferably, said first angle lies in the range 5° to
10 45°.

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12 Preferably, said first angle lies in the range 5° to
13 25°.

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15 Preferably, said at least one inlet port is an aerosol
16 inlet port for providing aerosol droplets of a dopant
17 ion solution to said burner.

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19 DESCRIPTION OF THE DRAWINGS

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21 Embodiments of the present invention will now be
22 described by way of example only, with reference to the
23 drawings in which:

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25 Fig. 1 is an FHD burner already known in the prior art;

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Fig. 2 is a cross-section through an FHD burner of the type shown in Fig. 1; and

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30 Fig. 3 is a cross-section through a modified FHD burner
31 according to the present invention.

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33 DETAILED DESCRIPTION OF THE INVENTION

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35 Referring to the drawings, Fig. 1 illustrates a FHD
36 burner 1 already known in the art. The burner 1 has

1 four feed inlet ports: a halide inlet port 2, a
2 hydrogen inlet port 3, an aerosol inlet port 4, and an
3 oxygen inlet port 5. The halide inlet port 2 feeds the
4 burner 1 with halide deposition materials, for example,
5 SiCl_3 , PCl_3 , etc carried by a suitable carrier gas, for
6 example, N_2 . The inlet ports 2,3 4 and 5 communicate
7 with a gas mixing region 8 at the output of the burner
8 1.

9
10 The aerosol inlet port 4 supplies aerosol droplets of a
11 dopant ion solution, for example, 0.2 M aqueous ErCl_3 .
12 An atomizer 6 is used to generate the aerosol droplets
13 of the dopant ion solution. The aerosol droplets are
14 carried by a carrier gas, for example, N_2 to the aerosol
15 inlet port 4 of the burner 1. The water solvent is
16 then evaporated to leave submicron particles of the
17 dopant ions (here Er^{+3}) which are prone to condense at
18 the inlet port 4. For solution strengths above 0.2M,
19 the build up of condensed dopant ions can create a
20 blockage 7 which can clog the inlet port 4. This
21 blockage 7 occurs before the dopant ions react in the
22 gas mixing reaction zone 8, which affects the rate at
23 which the dopant ions are incorporated during
24 fabrication of a waveguide 9. The blockage 7 arises
25 due to the combination of an abrupt reduction in pipe
26 volume and the change in directionality of the carrier
27 gas flow ($\theta = 68^\circ$ from the torch axis (X in Fig. 1)).
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29 Referring now to Fig. 2, there is shown a cross-section
30 through this type of conventional burner 1. The inlet
31 ports 2, 3, 4 and 5 are all aligned at the same angle θ
32 to the torch axis X, and transfer the feed gases (the
33 gas carrying the halide deposition materials, hydrogen,
34 the gas carrying the dopant ions, and oxygen) into
35 concentric torch conduits 10, 11, 12 and 13
36 respectively. The halide torch conduit 10, hydrogen

torch conduit 11, aerosol torch conduit 12, and oxygen torch conduit 13 deliver the feed gases to the gas mixing reaction zone 8 located in the burner nozzle 14 where the dopant ions are oxidised in the burner flame. The oxidised dopant ions are then incorporated during the deposition of the layers (not shown) which form the waveguide 9 (shown in Fig.1) a single step process.

Referring now to Fig. 3, there is shown a modified burner 15 made in accordance with the invention for introducing rare earth dopant ions, for example, Er^{+3} , during fabrication of a waveguide (not shown).

The burner 15 has four feed inlet ports: a halide inlet port 16, a hydrogen inlet port 17, an aerosol inlet port 18, and an oxygen inlet port 19. The halide inlet port 16 supplies the deposition materials, for example, SiCl_3 , PCl_3 , etc, which are carried by a suitable carrier gas, for example, N_2 . The aerosol inlet port 18 supplies aerosol droplets of a dopant ion solution, for example, aqueous ErCl_3 .

The halide inlet port 16, hydrogen port 17, and oxygen port 19 are located in the same radial plane radiating from the torch axis Y and can be all aligned at the same angle θ_1 to the torch axis Y. The aerosol inlet port 18 is located in a different radial plane (for example, it may be displaced by 180° from the plane in which the inlet ports 16, 17 and 19 are located) and is positioned at a different angle θ_2 with respect to the torch axis Y. The inlet ports 16, 17, 18 and 19 transfer the feed gases into respective concentric torch conduits 20, 21, 22 and 23. The halide torch conduit 20, hydrogen torch conduit 21, aerosol torch conduit 22, and oxygen torch conduit 23 deliver their respective feed gases to a gas mixing reaction zone 24

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1 for example upstream along the aerosol inlet port 18 or
2 downstream along the aerosol conduit 22.

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4 The prevention of a blockage occurring as the dopant
5 ions enter the aerosol conduit 22 is further assisted
6 by reducing the angle of directionality θ_2 (the angle
7 the aerosol inlet port makes with the torch axis (Y in
8 Fig. 3)). In the preferred embodiment, significant
9 reduction in the amount of condensation is provided by
10 θ_2 being substantially equal to 10° , which is in a
11 preferred range of 5° to 25° . A reduction in the
12 amount of condensation is also achieved if θ_2 is in the
13 range of 25° to 45° .

14
15 The dimensions of the aerosol conduit 22 are selected
16 to optimise the dopant process and to provide
17 directionality to the flame whilst reducing the burner
18 nozzle 26 temperature to below 1300°C . This prevents
19 devitrification of the nozzle 26 which would otherwise
20 provide unwanted contaminants.

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22 In the preferred embodiment, with a deposition rate of
23 $1\text{ }\mu\text{m}$ of base material per traversal of the FHD burner,
24 it is possible to achieve doping levels of up to 0.72
25 wt% for an ErCl_3 solution strength of 1M with a carrier
26 gas flow rate of $2.4\text{ litre min}^{-1}$. Higher dopant levels
27 can be achieved, for example, by maintaining the rare
28 earth dopant conditions and reducing the halide flow
29 rates or by increasing the concentration of the rare
30 earth dopant solution.

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32 Other dopant ions, for example, rare earth or heavy
33 metal ions and combinations of ions can be incorporated
34 using the burner 15 into the deposition stage.
35 Suitable solutions including rare earth and/or heavy
36 metal ions can be prepared at much higher

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